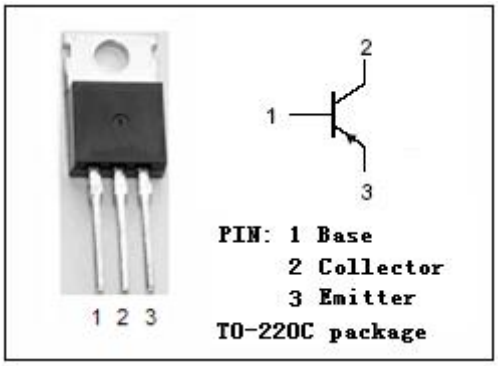
isc Silicon PNP Power Transistor — 2SB1064



DESCRIPTION

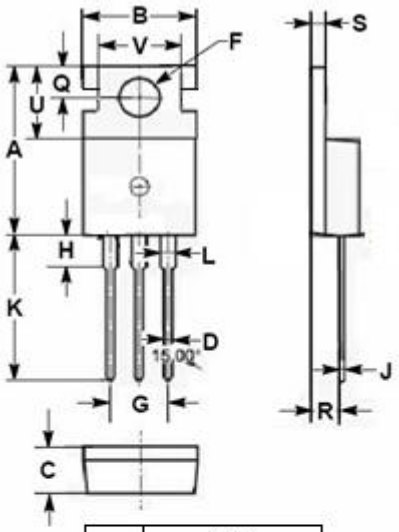
- Low Collector Saturation Voltage
  : $V_{CE(sat)}$= -1.0V(Max)@I_C= -2A
- Wide Area of Safe Operation
- Complement to Type 2SD1505
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-3	A
I_{CM}	Collector Current-Peak	-4.5	A
P_C	Total Power Dissipation @ T_a=25℃	1.5	W
	Total Power Dissipation @ T_C=25℃	30	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -1mA ; I_B= 0	-50			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -50 μ A; I_E= 0	-60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -50 μ A; I_C= 0	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -2A; I_B= -0.2A			-1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -2A; I_B= -0.2A			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -40V; I_E= 0			-1.0	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= -4V; I_C= 0			-1.0	μ A
h_{FE}	DC Current Gain	I_C= -0.5A; V_{CE}= -3V	60		320	
f_T	Current-Gain—Bandwidth Product	I_C= -0.5A; V_{CE}= -5V		70		MHz
C_{OB}	Output Capacitance	I_E=0; V_{CB}= -10V; f= 1MHz		50		pF

◆ **h_{FE} Classifications**

D	E	F
60-120	100-200	160-320